- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

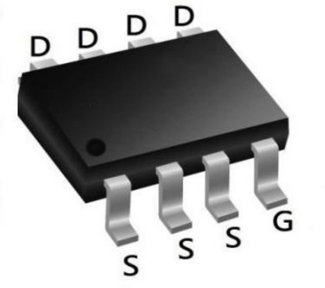
BVDSS	RDSON	ID
20V	4.8 mΩ	20A

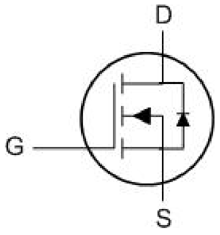
Description

The XXW20N02S is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XXW20N02S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

SOP8 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	20	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V[1]	11	A
I_{DM}	Pulsed Drain Current[2]	80	A
EAS	Single Pulse Avalanche Energy[3]	48	mJ
I_{AS}	Avalanche Current	11	A
P_D@T_C=25˚C	Total Power Dissipation[4]	38	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	4.2	˚C/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.4	0.7	1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=4.5V, I_D=10A	-	4.8	6.5	mΩ
		V_{GS}=2.5V, I_D=5A	-	6.8	10	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1.0MHz	-	1832	-	pF
C_{oss}	Output Capacitance		-	289	-	pF
C_{rss}	Reverse Transfer Capacitance		-	271	-	pF
Q_g	Total Gate Charge	V_{DS}=10V, I_D=10A, V_{GS}=4.5V	-	23	-	nC
Q_{gs}	Gate-Source Charge		-	4.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	7.3	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V, I_D=10A, R_{GEN}=3Ω, V_{GS}=4.5V	-	15	-	ns
t_r	Turn-on Rise Time		-	37	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	52	-	ns
t_f	Turn-off Fall Time		-	21	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=10A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	IF=25A,dI/dt=100A/μs	-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	21	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=10V, V_G=4.5V, L=0.5mH, R_G=25Ω, I_{AS}=4.8A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Performance Characteristics

Figure1: Output Characteristics

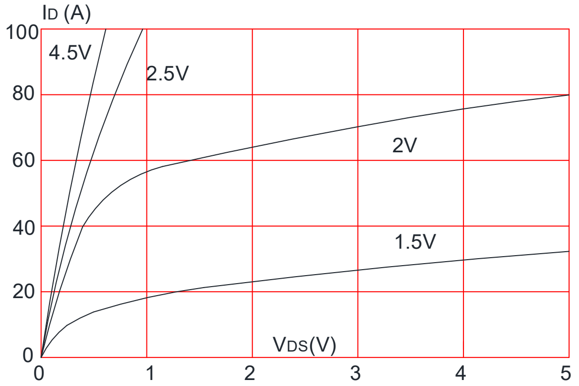


Figure 2: Typical Transfer Characteristics

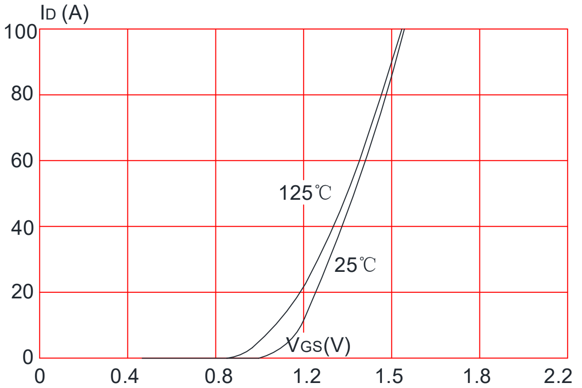


Figure 3: On-resistance vs. Drain Current

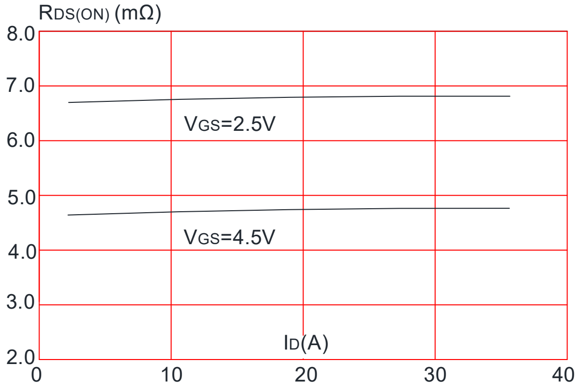


Figure 4: Body Diode Characteristics

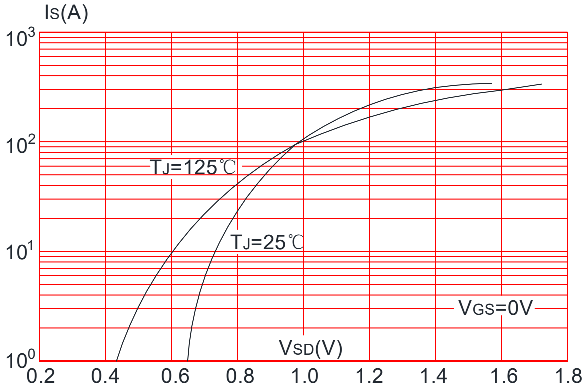


Figure 5: Gate Charge Characteristics

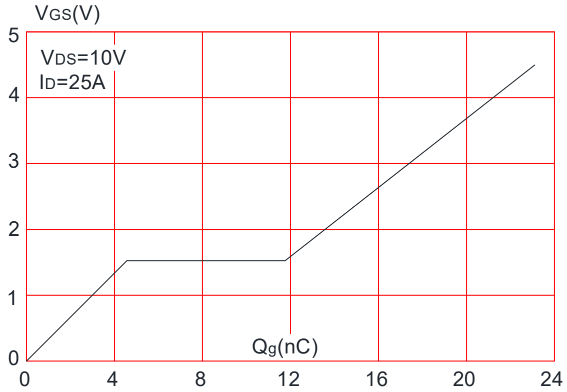


Figure 6: Capacitance Characteristics

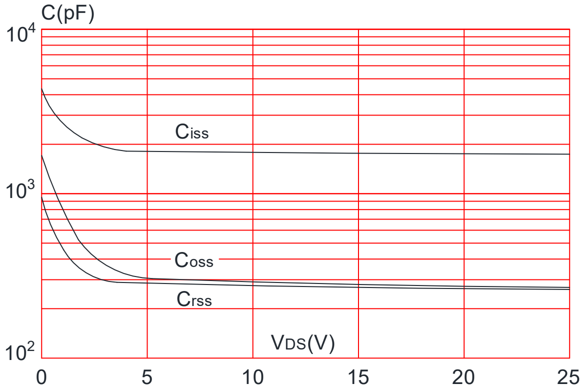


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

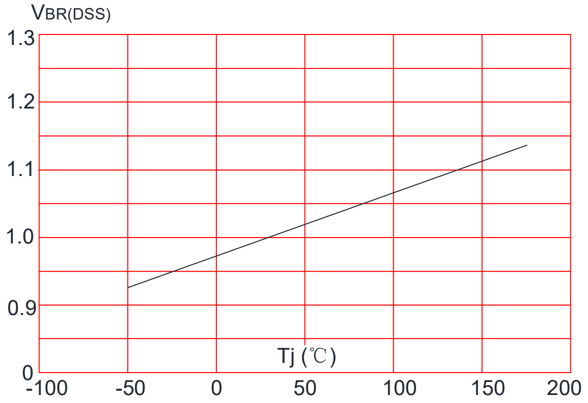


Figure 8: Normalized on Resistance vs. Junction Temperature

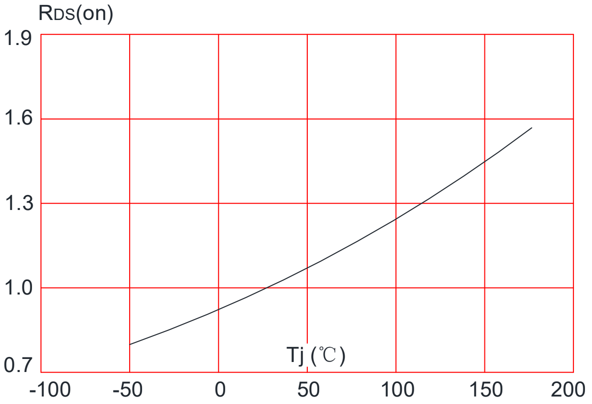


Figure 9: Maximum Safe Operating Area

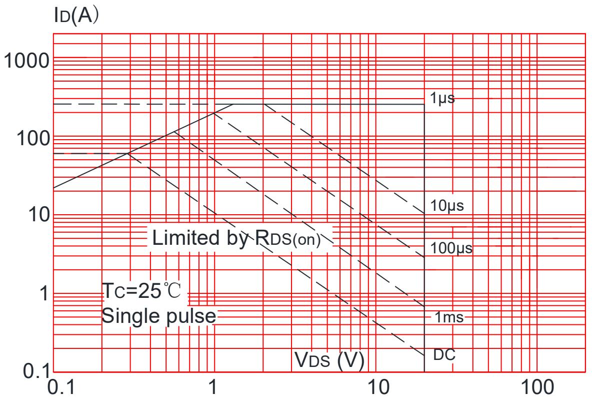


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

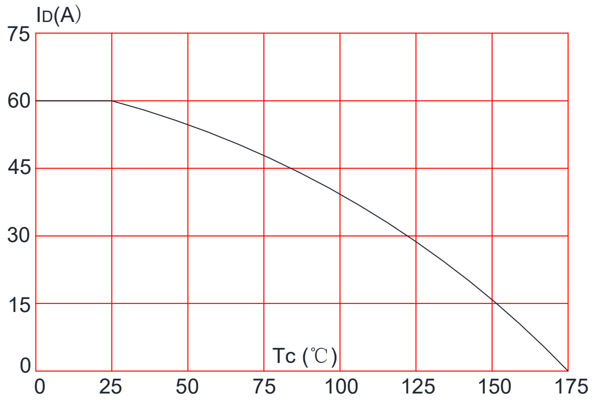
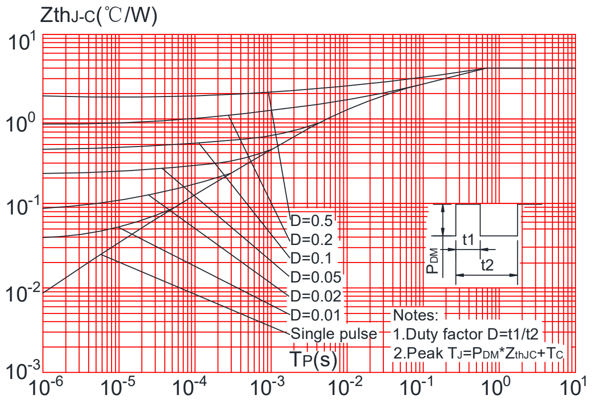
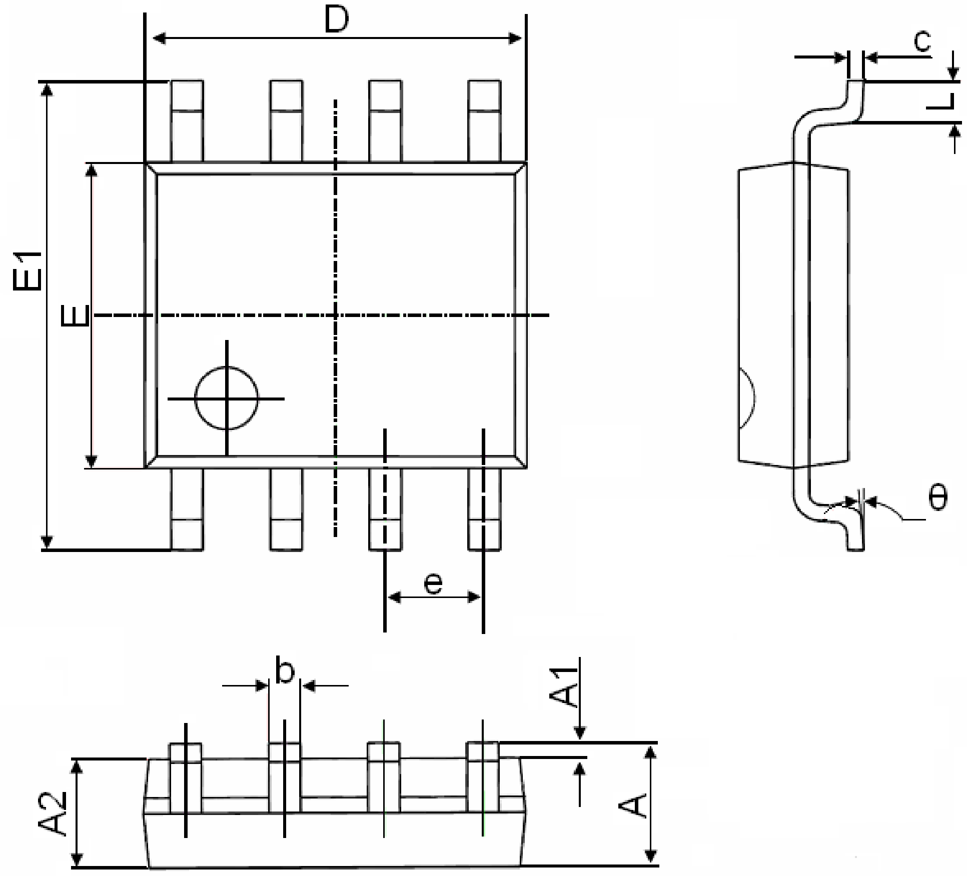


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Notes:
1.Duty factor D=t1/t2
2.Peak $T_J=P_{DM}*Z_{thJC}+T_C$

Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	**Max.**	**Min.**	**Max.**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°